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# NCE25G135P

# 1350V, 25A, Trench NPT IGBT

### Features

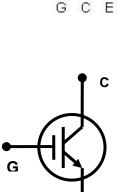
- Trench NPT( Non Punch Through) IGBT
- High speed switching
- Low saturation voltage: V<sub>CE(sat)</sub>=2.0V@I<sub>C</sub>=25A
- High input impedance

### Applications

- Inductive heating, Microwave oven, Inverter, UPS, etc.
- Soft switching applications

### **General Description**

Using advanced Trench NPT technology, NCE's 1350V IGBTs offers superior conduction and switching performances, and easy parallel operation with exceptional avalanche ruggedness. This device is designed for soft switching applications.



## **Absolute Maximum Ratings**

Symbol	Description	Ratings	Units
V <sub>CES</sub>	Collector to Emitter Voltage	1350	V
V <sub>GES</sub>	Gate to Emitter Voltage	+/-30	V
Ι <sub>C</sub>	Continuous Collector Current @T <sub>C</sub> =25°C	50	Α
	Continuous Collector Current @T <sub>C</sub> =100°C	25	Α
I <sub>CM</sub> (1)	Pulsed Collector Current	90	A
P <sub>D</sub>	Maximum Power Dissipation @T <sub>C</sub> =25°C	312	W
	Maximum Power Dissipation @T <sub>C</sub> =100°C	125	W
TJ	Operating Junction Temperature	-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range	-55 to +150	°C
	Maximum Lead Temp. for soldering Purposes, 1/8" from		
TL	case for 5seconds	300	°C

#### Notes:

1. Repetitive rating, Pulse width limited by max. junction temperature



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### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units
R <sub>JC</sub>	Thermal Resistance, Junction to Case	-	0.4	°C/W
R <sub>JA</sub>	Thermal Resistance, Junction to Ambient	-	40	°C/W

## Electrical Characteristics of the IGBT $\tau_{c=25^\circ\text{C}}$

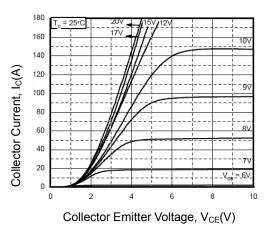
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Char	acteristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	V <sub>GE</sub> =0V, Ic=1mA	1350	-	-	V
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE}$ =1350V, $V_{GE}$ =0V	-	-	1	mA
I <sub>GES</sub>	G-E Leakage Current	$V_{GE}$ =20V, $V_{CE}$ =0V	-	-	+/-250	nA
On Char	acteristics					
$V_{GE(th)}$	G-E Threshold Voltage	I <sub>C</sub> =25mA, V <sub>CE</sub> =V <sub>GE</sub>	4.0	5.5	7.0	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation	I <sub>C</sub> =25A, V <sub>GE</sub> =15V T <sub>C</sub> =25°C	-	2	2.5	V
	Voltage	I <sub>C</sub> =25A, V <sub>GE</sub> =15V T <sub>C</sub> =125°C	-	2.15	-	V
Dynamic	Characteristics					
C <sub>ies</sub>	Input Capacitance		-	3700	-	pF
C <sub>oes</sub>	Output Capacitance	V <sub>CE</sub> =30V, V <sub>GE</sub> =0V,	-	130	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	f=1MHz	-	80	-	pF
Switchin	g Characteristics		1			
t <sub>d(on)</sub>	Turn-On Delay Time		-	50	-	ns
t <sub>r</sub>	Rise Time		_	60	90	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC}$ =600V,I <sub>C</sub> =25A,	-	190	-	ns
t <sub>f</sub>	Fall Time	R <sub>G</sub> =10Ώ,V <sub>GE</sub> =15V,	-	100	180	ns
Eon	Turn-On Switching Loss	Resistive Load,	-	4.1	6.2	mJ
E <sub>off</sub>	Turn-Off Switching Loss	T <sub>C</sub> =25°C	-	0.96	1.5	mJ
E <sub>ts</sub>	Total Switching Loss		-	5.06	7.7	mJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	50	-	ns
tr	Rise Time		-	60	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>CC</sub> =600V,I <sub>C</sub> =25A,	-	200	-	ns
t <sub>f</sub>	Fall Time	$R_{G}$ =10 $\Omega$ , $V_{GE}$ =15V,	-	154	-	ns
Eon	Turn-On Switching Loss	Resistive Load, T <sub>c</sub> =125°C	-	4.3	6.9	mJ
E <sub>off</sub>	Turn-Off Switching Loss	1C-120 C	-	1.5	2.4	mJ
E <sub>ts</sub>	Total Switching Loss		-	5.8	9.3	mJ
Qg	Total Gate Charge		-	200	300	nC
Q <sub>ge</sub>	Gate to Emitter Charge	V <sub>CC</sub> =600V,I <sub>C</sub> =25A, V <sub>GE</sub> =15V	-	15	23	nC
Q <sub>gc</sub>	Gate to Collector Charge	V <sub>GE</sub> =15V	-	100	150	nC

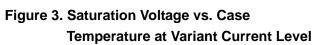


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## **Typical Performance Characteristics**

### Figure 1. Typical Output Characteristics





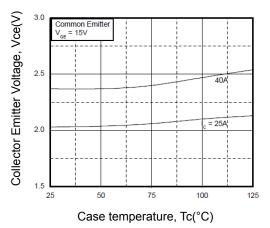


Figure 5. Saturation Voltage vs.  $V_{\text{GE}}$ 

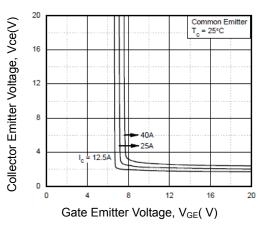


Figure 2. Typical Saturation Voltage Characteristics

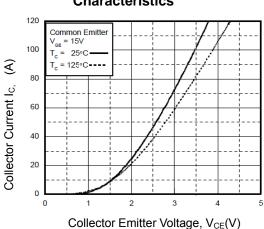


Figure 4. Saturation Voltage vs. V<sub>GE</sub>

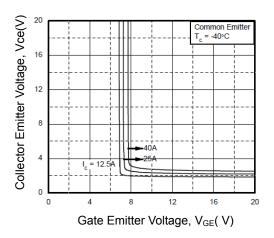
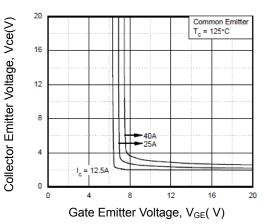


Figure 6. Saturation Voltage vs.  $V_{GE}$ 



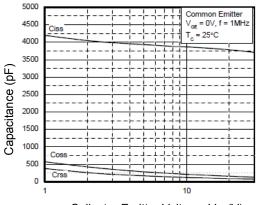




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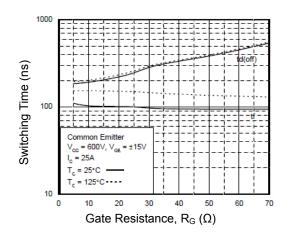
## **Typical Performance Characteristics (Continued)**

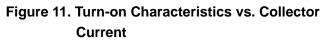
#### Figure 7. Capacitance Characteristics

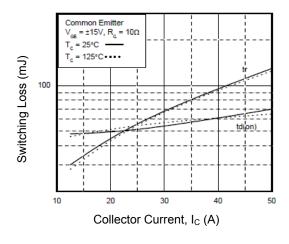


Collector Emitter Voltage, V<sub>CE</sub>(V)

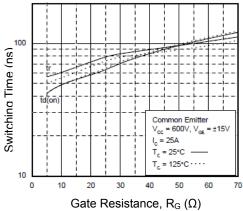
#### Figure 9. Turn-off Characteristics vs. Gate Resistance

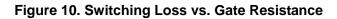






#### Figure 8. Turn-on Characteristics vs. Gate Resistance





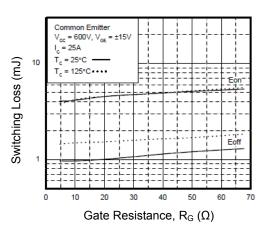
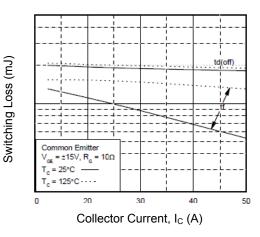


Figure 12. Turn-Off Characteristics vs. **Collector Current** 





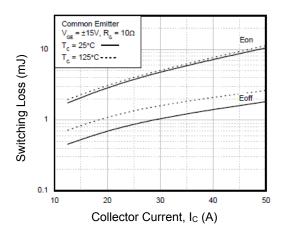


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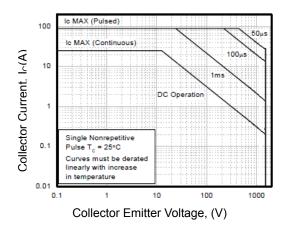
## **Typical Performance Characteristics (Continued)**

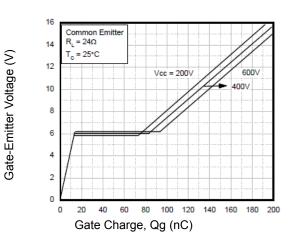
#### Figure 13. Switching Loss vs. Collector Current

#### Figure14. Gate Charge Characteristics

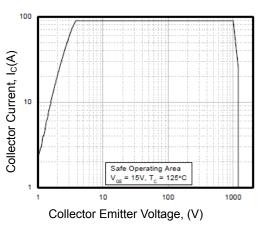


**Figure 15. SOA Characteristics** 









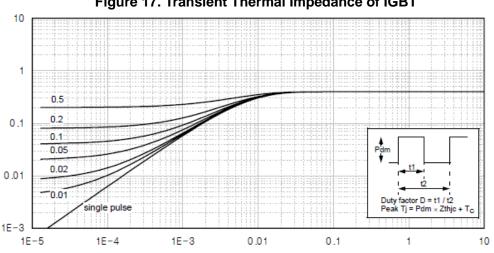
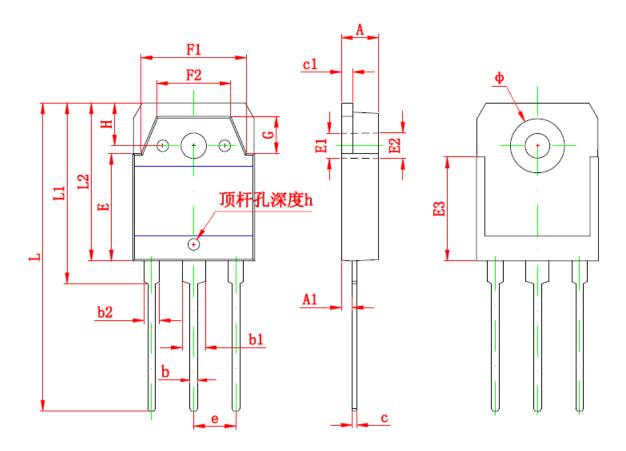


Figure 17. Transient Thermal Impedance of IGBT



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# **TO-3P Mechanical Dimensions (continued)**



Symbol	Dimensions	In Millimeters	Dimensior	is in inches		
Symbol	Min	Max	Min	Max		
A	4.600	5.000	0.181	0.197		
A 1	1.200	1.600	0.047	0.063		
b	0.800	1.200	0.031	0.047		
b1	2.800	3.200	0.110	0.126		
b2	1.800	2.200	0.071	0.087		
С	0.500	0.700	0.020	0.028		
c1	1.450	1.650	0.057	0.065		
D	15.450	15.850	0.606	0.622		
E	13.700	14.100	0.539	0.555		
E 1	3.200	3.200 REF		0.126 REF		
E 2	3.300	3.300 REF		0.130 REF		
E 3	13.45	OREF	0.530 REF			
F 1	13.400	13.800	0.528	0.543		
F 2	9.400	9.800	0.370	0.386		
L	39.900	40.300	1.571	1.587		
L1	23.200	23.600	0.913	0.929		
L2	20.300	20.600	0.799	0.811		
Ф	6.900	7.100	0.272	0.280		
G	5.150	5.550	0.203	0.219		
e	5.450 TYP		0.215 TYP			
Н	5.000	REF	0.19	7 REF		
h	0.000	0.300	0.000	0.012		





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